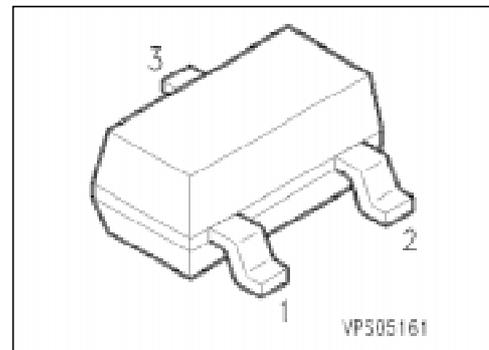


## Silicon Switching Diode Array

**BAV 74**

- For high-speed switching
- Common cathode



| Type   | Marking | Ordering Code (tape and reel) | Pin Configuration | Package <sup>1)</sup> |
|--------|---------|-------------------------------|-------------------|-----------------------|
| BAV 74 | JAs     | Q62702-A693                   |                   | SOT-23                |

### Maximum Ratings per Diode

| Parameter  | Symbol    | Values         | Unit             |
|--|-----------|----------------|------------------|
| Reverse voltage  | $V_R$     | 50             | V                |
| Peak reverse voltage                                       | $V_{RM}$  | 50             |                  |
| Forward current  | $I_F$     | 200            | mA               |
| Surge forward current, $t = 1 \mu s$                       | $I_{FS}$  | 4.5            | A                |
| Total power dissipation, $T_s = 35 \text{ }^\circ\text{C}$ | $P_{tot}$ | 250            | mW               |
| Junction temperature                                       | $T_j$     | 150            | $^\circ\text{C}$ |
| Storage temperature range                                  | $T_{stg}$ | - 65 ... + 150 |                  |

### Thermal Resistance

|                                  |             |            |     |
|----------------------------------|-------------|------------|-----|
| Junction - ambient <sup>2)</sup> | $R_{th JA}$ | $\leq 600$ | K/W |
| Junction - soldering point       | $R_{th JS}$ | $\leq 460$ |     |

<sup>1)</sup> For detailed information see chapter Package Outlines.

<sup>2)</sup> Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm<sup>2</sup> Cu.

**Electrical Characteristics per Diode**  
at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

| Parameter | Symbol | Values |      |      | Unit |
|-----------|--------|--------|------|------|------|
|           |        | min.   | typ. | max. |      |

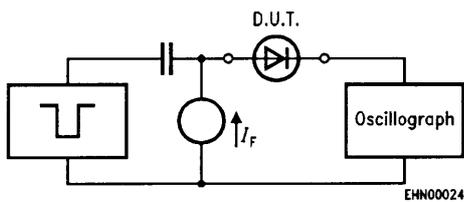
**DC characteristics**

|  |            |    |   |            |               |
|--|------------|----|---|------------|---------------|
| Breakdown voltage<br>$I_{(BR)} = 100\text{ }\mu\text{A}$                                       | $V_{(BR)}$ | 50 | – | –          | V             |
| Forward voltage<br>$I_F = 100\text{ mA}$   | $V_F$      | –  | – | 1          |               |
| Reverse current<br>$V_R = 50\text{ V}$<br>$V_R = 50\text{ V}, T_A = 150\text{ }^\circ\text{C}$ | $I_R$      | –  | – | 0.1<br>100 | $\mu\text{A}$ |

**AC characteristics**

|   |          |   |   |   |    |
|---|----------|---|---|---|----|
| Diode capacitance<br>$V_R = 0\text{ V}, f = 1\text{ MHz}$   | $C_D$    | – | – | 2 | pF |
| Reverse recovery time<br>$I_F = 10\text{ mA}, I_R = 10\text{ mA}, R_L = 100\text{ }\Omega$<br>measured at $I_R = 1\text{ mA}$ | $t_{rr}$ | – | – | 4 | ns |

**Test circuit for reverse recovery time**

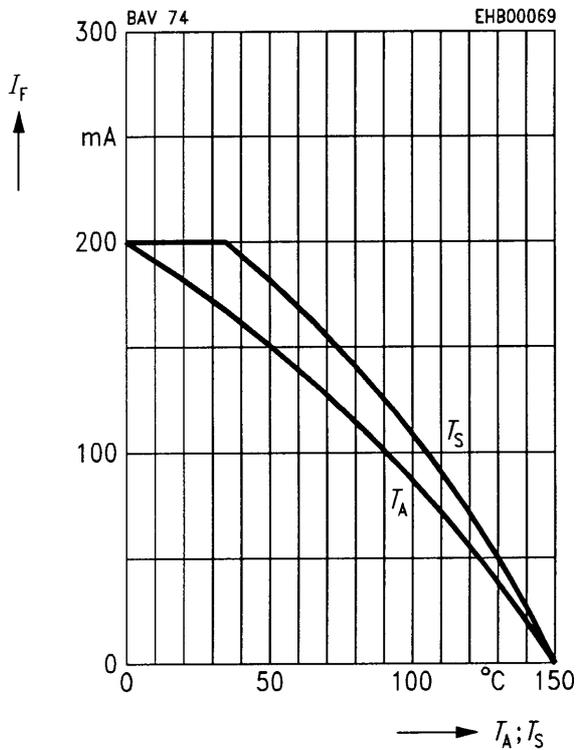


Pulse generator:  $t_p = 100\text{ ns}, D = 0.05$   
 $t_r = 0.6\text{ ns}, R_j = 50\text{ }\Omega$

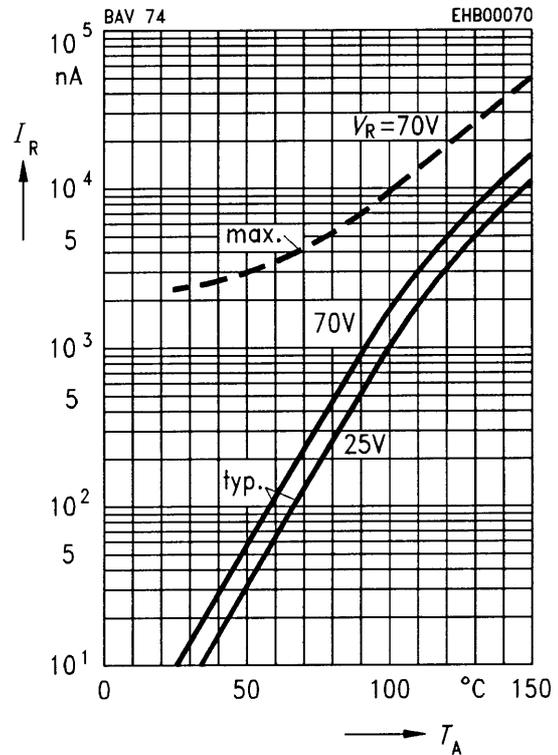
Oscilloscope:  $R = 50\text{ }\Omega$   
 $t_r = 0.35\text{ ns}$   
 $C \leq 1\text{ pF}$

### Forward current $I_F = f(T_A^*; T_S)$

\* Package mounted on epoxy

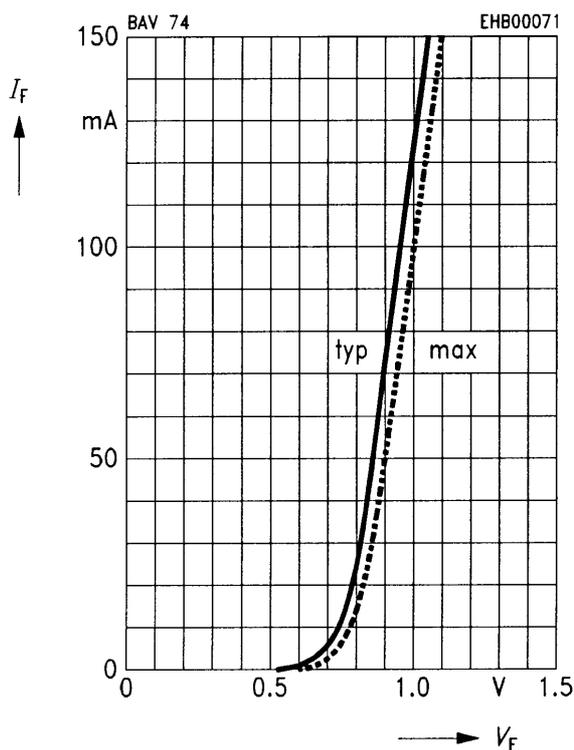


### Reverse current $I_R = f(T_A)$



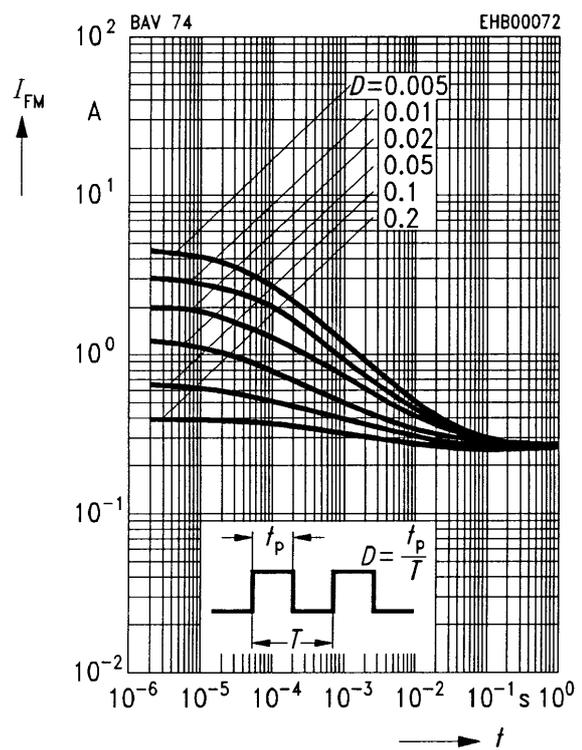
### Forward current $I_F = f(V_F)$

$T_A = 25\text{ °C}$



### Peak forward current $I_{FM} = f(t)$

$T_A = 25\text{ °C}$



Forward voltage  $V_F = f(T_A)$

